



60V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	Max R _{DS(on)}	Max I _D T _A = +25°C		
-60V	400mΩ @ V _{GS} = -10V	-1.1A		
	600mΩ @ V _{GS} = -4.5V	-0.9A		

Description

This MOSFET utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed, making it ideal for high-efficiency power management applications.

Applications

- DC-DC Converters
- Power Management Functions
- · Relay and Solenoid Driving
- Motor Control

Features

- · Fast switching speed
- Low input capacitance
- · Low gate charge
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

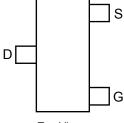
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 ³
- Weight: 0.008 grams (approximate)

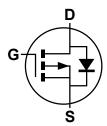




Top View



Top View Pin Out



Equivalent Circuit

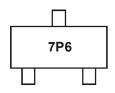
Ordering Information (Notes 4)

Product	Compliance	Case	Packaging
ZXMP6A13FTA	Standard	SOT23	3,000 / Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



7P6 = Product Type Marking Code



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units	
Drain-Source Voltage			V_{DSS}	-60	V	
Gate-Source Voltage			V_{GS}	±20	V	
Continuous Drain Current	V _{GS} = -10V	T _A = +70°C	(Note 7) (Note 7) (Note 6)	I _D	-1.1 -0.8 -0.9	А
Pulsed Drain Current (Note 7)				I_{DM}	-4	A
Continuous Source Current (Body Diode) (Note 6)				ls	-1.2	Α
Pulsed Source Current (Body Diode) (Note 7)				I _{SM}	-4	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	D	625	mW
Linear Derating Factor	P _D	5	mW/°C
Power Dissipation (Note 6)	D	806	mW
Linear Derating Factor	P _D	6.5	mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	200	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	155	°C/W
Thermal Resistance, Junction to Leads (Note 8)	R ₀ JL	194	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

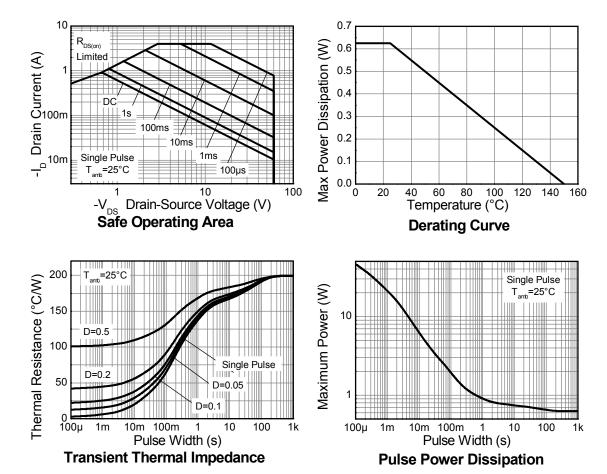
- 5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions 6. For a device surface mounted on FR4 PCB measured at t ≤ 5secs.

 7. Repetitive rating 25mm x 25mm FR4 PCB, D = 0.05 pulse width = 10μs pulse current limited by maximum junction temperature.

 8. Thermal resistance from junction to solder-point (at the end of the collector lead).



Thermal Characteristics





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

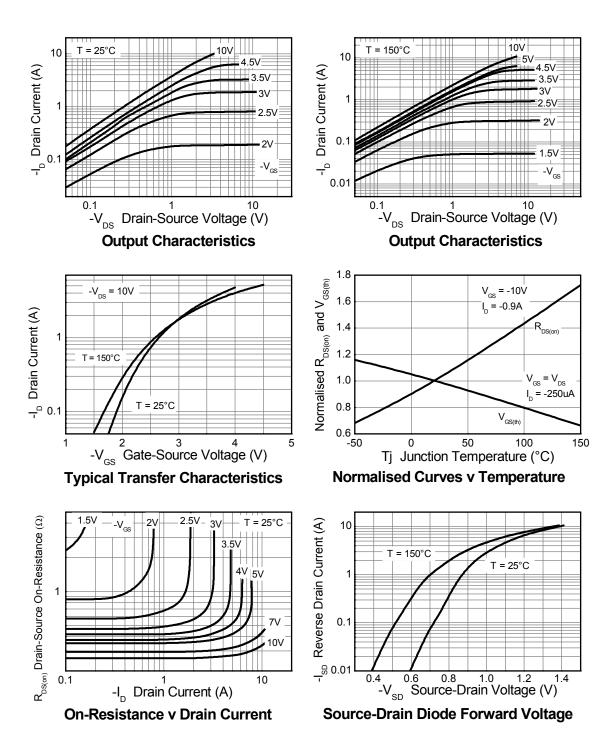
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	-60	_	_	V	$I_D = -250 \mu A$, $V_{GS} = 0V$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-0.5	μA	V _{DS} = -60V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS	ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(th)}	-1	_	-3	V	$I_D = -250 \mu A$, $V_{DS} = V_{GS}$	
Static Drain-Source On-Resistance (Note 9)	D			0.400	Ω	$V_{GS} = -10V, I_D = -0.9A$	
Static Dialii-Source Off-Resistance (Note 9)	R _{DS (ON)}	_	_	0.600	1 12	V_{GS} = -4.5V, I_{D} = -0.8A	
Forward Transconductance (Notes 9 & 11)	g fs	_	1.8	_	S	$V_{DS} = -15V, I_D = -0.9A$	
Diode Forward Voltage (Note 9)	V _{SD}	_	-0.85	-0.95	V	$T_J = +25^{\circ}C$, $I_S = -0.8A$, $V_{GS} = 0V$	
Reverse Recovery Time (Note 11)	t _{rr}	_	21.1	_	ns	$T_J = +25^{\circ}C$, $I_F = -0.9A$,	
Reverse Recovery Charge (Note 11)	Qrr	_	19.3	_	nC	di/dt = 100A/μs	
DYNAMIC CHARACTERISTICS (Note 11)							
Input Capacitance	C _{iss}	_	219	_			
Output Capacitance	Coss	_	25.7	_	pF	$V_{DS} = -30V, V_{GS} = 0V$ f = 1MHz	
Reverse Transfer Capacitance	C _{rss}	_	20.5	_			
Turn-On Delay Time (Note 10)	t _{D(on)}	_	1.6	_			
Turn-On Rise Time (Note 10)	t _r	_	2.2	_		V_{DD} = -30V, I_D = -1A, $R_G \cong 6.0\Omega$, V_{GS} = -10V	
Turn-Off Delay Time (Note 10)	t _{D(off)}	_	11.2	_	ns		
Turn-Off Fall Time (Note 10)	t _f	_	5.7	_			
Total Gate Charge (Note 10)	Qg	_	2.9	_	nC	$V_{DS} = -30V$, $V_{GS} = -4.5V$, $I_D = -0.9A$	
Total Gate Charge (Note 10)	Qg	_	5.9	_		.,	
Gate-Source Charge (Note 10)	Q _{gs}	_	0.74	_	nC	$V_{DS} = -30V, V_{GS} = -10V,$ $I_{D} = -0.9A$	
Gate-Drain Charge (Note 10)	Q _{gd}	_	1.5	_		D0.9A	

Notes:

Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤ 2%.
 Switching characteristics are independent of operating junction temperature.
 For design aid only, not subject to production testing.

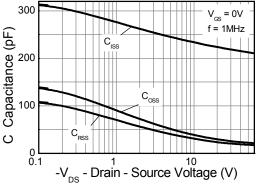


Typical Characteristics

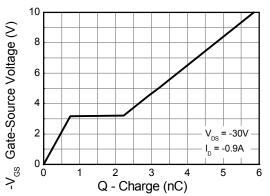




Typical Characteristics - (cont.)

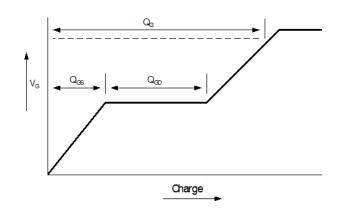


Capacitance v Drain-Source Voltage

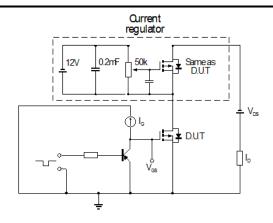


Gate-Source Voltage v Gate Charge

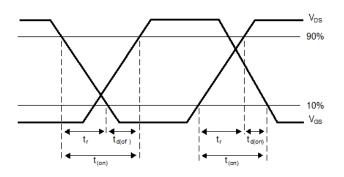
Test Circuits



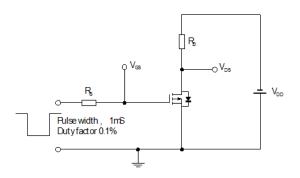
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms

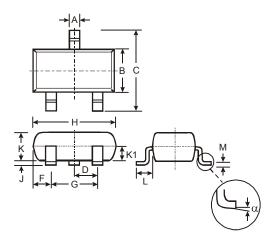


Switching time test circuit



Package Outline Dimensions

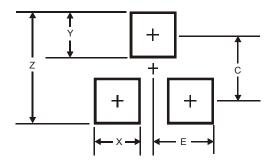
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.903	1.10	1.00		
K1	-	1	0.400		
L	0.45	0.61	0.55		
M	0.085	0.18	0.11		
α	0°	8°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
Z	2.9		
X	0.8		
Y	0.9		
С	2.0		
Е	1.35		



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